

# RJH65T04BDPM-A0

650V - 30A - IGBT Power Switching

R07DS1366EJ0200 Rev.2.00 Oct.05.2022

### **Features**

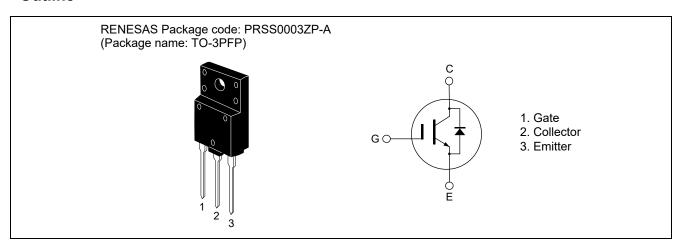
- Trench gate and thin wafer technology
- Built in fast recovery diode in one package
- Low collector to emitter saturation voltage  $V_{CE(sat)}$  = 1.5 V typ. (at I<sub>C</sub> = 30 A, V<sub>GE</sub> = 15 V, Ta = 25 °C)
- · Quality grade: Standard

- High speed switching  $t_f$  = 45 ns typ. (at V<sub>CC</sub> = 400 V, V<sub>GE</sub> = 15 V, I<sub>C</sub> = 30 A, Rg = 10  $\Omega$ , Ta=25 °C, inductive load)
- Operation frequency (20kHz ≤ f < 40kHz)
- Applications: Power Factor Correction circuit

## **Key Performance**

Туре	V <sub>CES</sub>	lc	V <sub>CE(sat)</sub> , T <sub>C</sub> =25°C	l <sub>F</sub>	Tj
RJH65T04BDPM-A0	650 V	30 A	1.5 V	50 A	175 °C

#### **Outline**



## **Absolute Maximum Ratings**

(Tc = 25 °C)

Item		Symbol	Ratings	Unit
Collector to emitter voltage		V <sub>CES</sub>	650	V
Gate to emitter voltage		V <sub>GES</sub>	±30	V
Collector current	Tc = 25 °C	lc	60	Α
	Tc = 100 °C	lc	30	Α
Collector peak current		IC(peak) Notes1	120	Α
Clamped inductive load c	urrent	I <sub>CL</sub> Notes2	120	Α
Diode forward current	Tc = 25 °C	lF	100	А
	Tc = 100 °C	lF	50	Α
Peak surge forward curre	nt	IFSM Notes3	230	Α
Collector power dissipation	on	P <sub>C</sub> Notes4	65	W
Junction temperature		Tj Notes4	175	°C
Storage temperature		Tstg	-55 to +150	°C

Note: Continuous heavy condition (e.g. high temperature/voltage/current or high variation of temperature) may affect a reliability even if it is within the absolute maximum ratings. Please consider derating condition for appropriate reliability in reference Renesas Semiconductor Reliability Handbook (Recommendation for Handling and Usage of Semiconductor Devices) and individual reliability data.

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1 %

- 2.  $V_{GE} = 15 V$
- 3. PW = 3 ms (sine half wave, Non-repetitive,1 cycle), Tj = 150 degC
- 4. Please use this device in the thermal conditions which the junction temperature does not exceed 175 °C Renesas IGBT Application Note is disclosed about reliability test and condition up to 175 °C

### **Thermal Resistance Characteristics**

(Tc = 25 °C)

Item	Symbol	Max. Value Notes5	Unit
Junction to case thermal resistance (IGBT)	R <sub>th(j-c)</sub>	2.3	°C/W
Junction to case thermal resistance (Diode)	R <sub>th(j-c)</sub>	2.35	°C/W

Notes: 5. Designed target value on Renesas measurement condition. (Not tested)

### **Electrical Characteristics**

(Tc = 25 °C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions	
Collector to emitter leakage current	Ices	_	_	100	μΑ	V <sub>CE</sub> = 650 V, V <sub>GE</sub> = 0 V	
Gate to emitter leakage current	Iges		_	±1	μΑ	V <sub>GE</sub> = ±30 V, V <sub>CE</sub> = 0 V	
Gate to emitter threshold voltage	$V_{GE(th)}$	4.0	_	7.0	V	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 1 mA	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	1.50	1.95	V	I <sub>C</sub> = 30 A, V <sub>GE</sub> = 15 V <sup>Notes6</sup>	
Input capacitance	Cies	_	1760	_	pF	V <sub>CE</sub> = 25 V	
Output capacitance	Coes	_	125	_	pF	V <sub>GE</sub> = 0 V	
Reverse transfer capacitance	Cres	_	34	_	pF	f = 1 MHz	
Total gate charge	Qg	_	74	_	nC	V <sub>GE</sub> = 15V	
Gate to emitter charge	Qge	_	13	_	nC	V <sub>CE</sub> = 400 V I <sub>C</sub> = 30 A	
Gate to collector charge	Qgc	_	31	_	nC		
Turn-on delay time	t <sub>d(on)</sub>	_	35	_	ns	V <sub>CC</sub> = 400 V	
Rise time	tr	_	25	_	ns	V <sub>GE</sub> = 15 V	
Turn-off delay time	$t_{d(off)}$	_	115	_	ns	I <sub>C</sub> = 30 A	
Fall time	t <sub>f</sub>	_	45	_	ns	$Rg = 10 \Omega$	
Turn-on loss energy	Eon	_	0.36	_	mJ	Inductive load Notes7	
Turn-off loss energy	E <sub>off</sub>	_	0.35	_	mJ		
Total switching energy	E <sub>total</sub>	_	0.71	_	mJ		
Turn-on delay time	t <sub>d(on)</sub>	_	35	_	ns	V <sub>CC</sub> = 400 V	
Rise time	tr	_	25	_	ns	V <sub>GE</sub> = 15 V	
Turn-off delay time	$t_{d(off)}$	_	125	_	ns	I <sub>C</sub> = 30 A	
Fall time	t <sub>f</sub>	_	70	_	ns	Rg = 10 Ω	
Turn-on loss energy	Eon	_	0.60	_	mJ	Tc = 150 °C Inductive load <sup>Notes7</sup>	
Turn-off loss energy	E <sub>off</sub>	_	0.50	_	mJ	inductive load	
Total switching energy	E <sub>total</sub>	_	1.10	_	mJ	]	
Diode forward voltage	VF		1.4	1.8	V	I <sub>F</sub> = 30 A <sup>Notes6</sup>	
Diode forward voltage	VF	_	1.7	2.2	V	I <sub>F</sub> = 50 A <sup>Notes6</sup>	
Diode reverse recovery time	t <sub>rr</sub>		80		ns	I <sub>F</sub> = 50 A, di <sub>F</sub> /dt = 300 A/μs	
		1		1	1	1	

0.35

7.5

μC

Α

Notes: 6. Pulse test

Diode reverse recovery charge

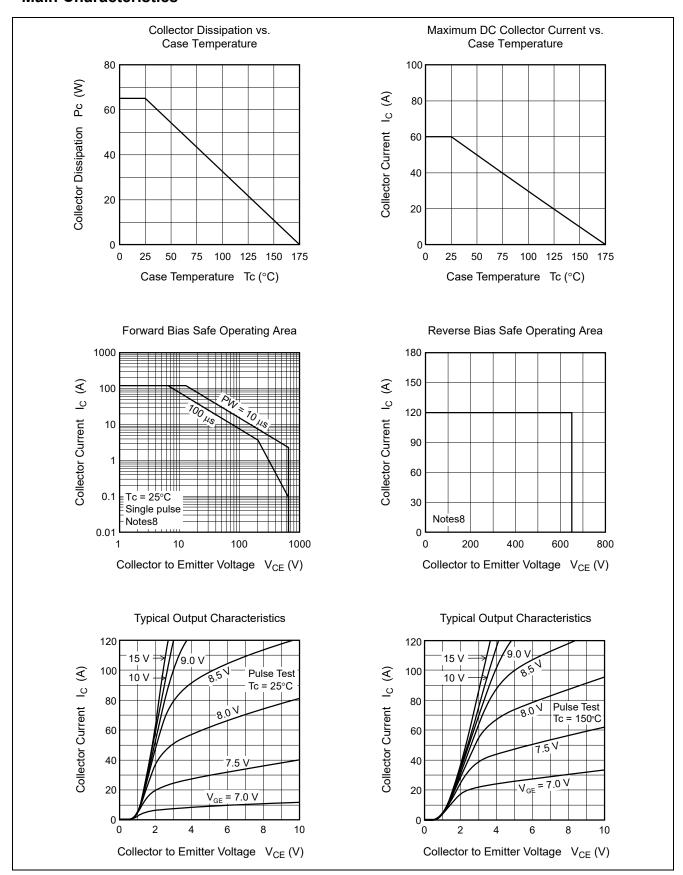
Diode peak reverse recovery current

7. Switching time test circuit and waveform are shown below.

 $Q_{rr}$ 

 $I_{\text{rr}}$ 

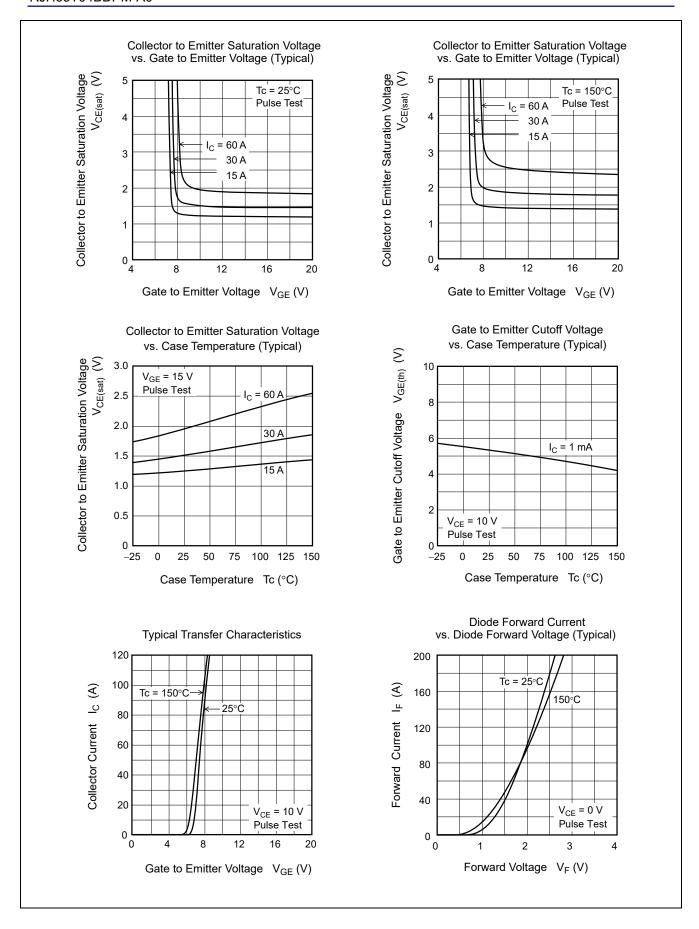
### **Main Characteristics**

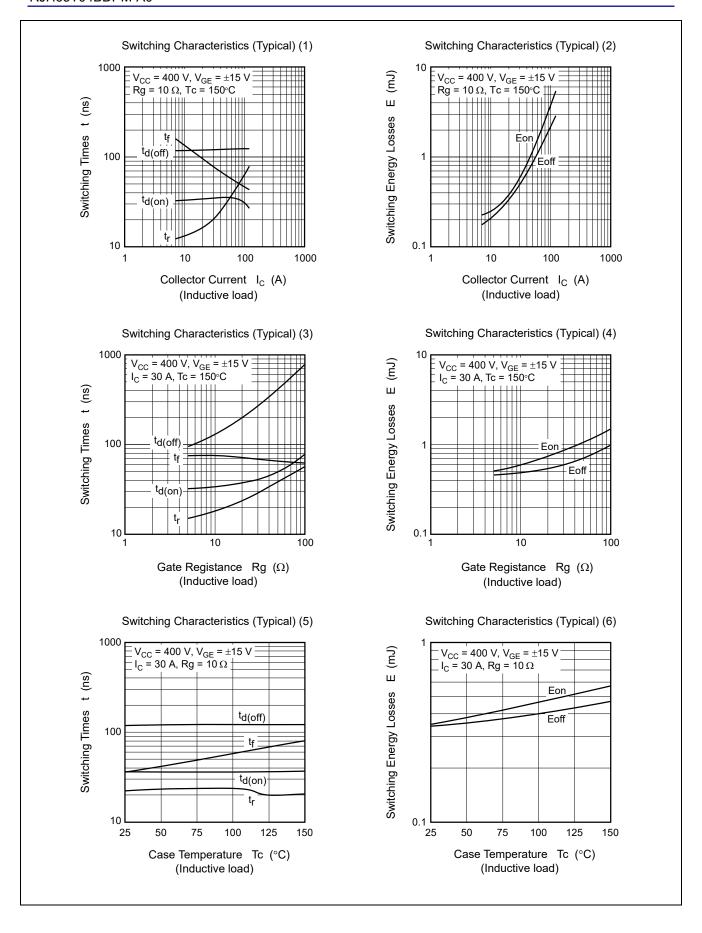


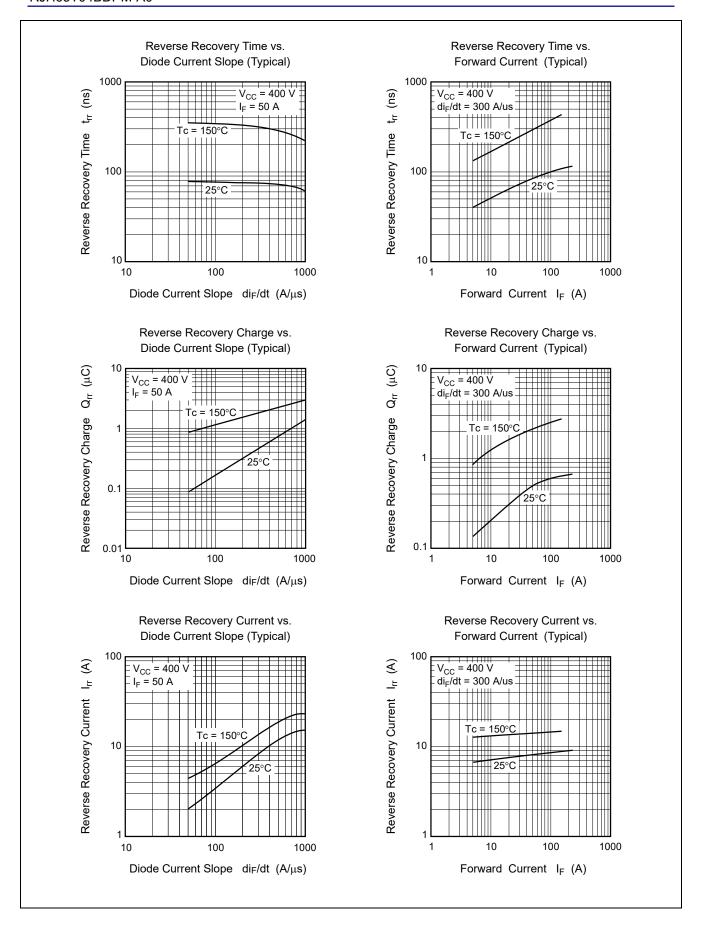
Notes: 8. Designed target value on Renesas measurement condition. (Not tested)

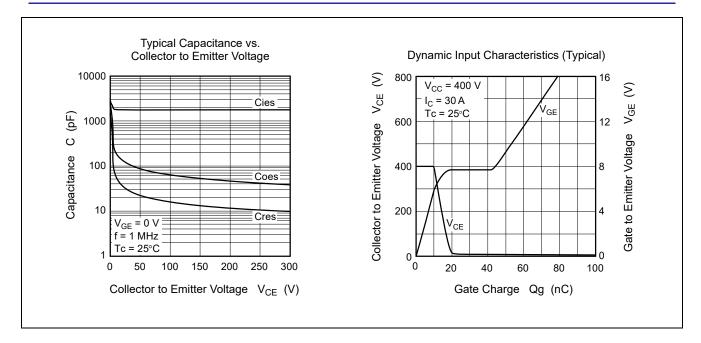
Renesas recommends that operating conditions are designed according to a document "Power MOS FET •

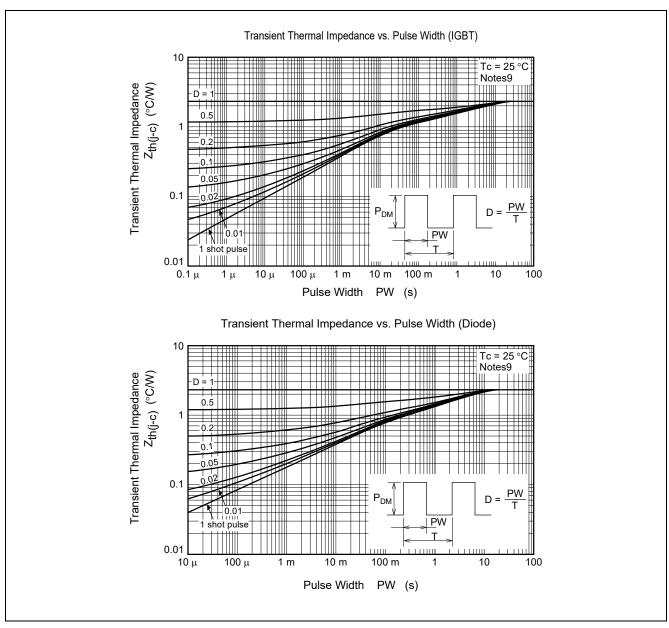
IGBT Attention of Handling Semiconductor Devices".



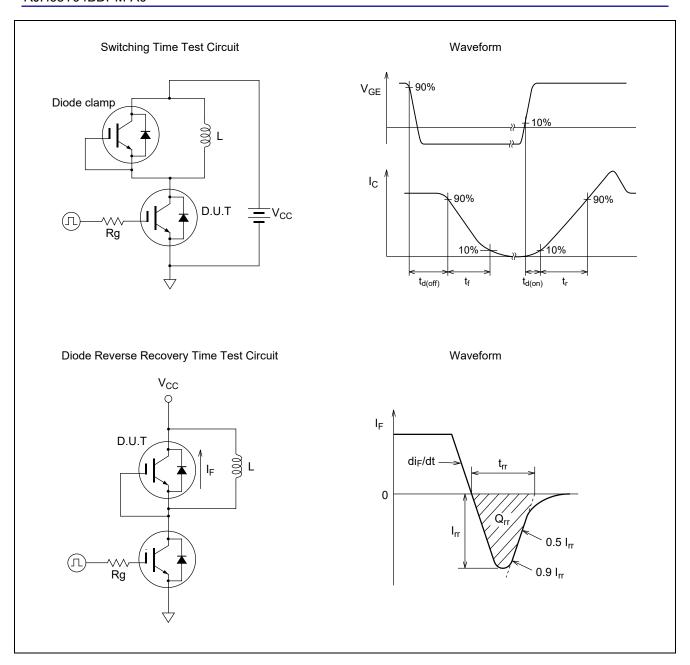




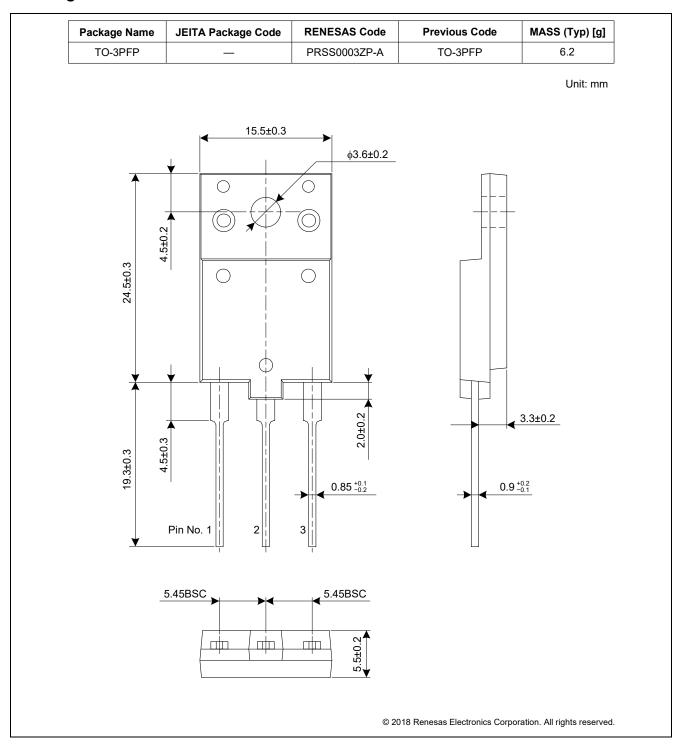




Notes: 9. Designed target value on Renesas measurement condition. (Not tested)



# **Package Dimensions**



# **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
RJH65T04BDPM-A0#T2	1000pcs	Box (tube)

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